



DMTH10H010SPS

100V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	Ι _D T _C = +25°C
100\/	8.8mΩ @ V _{GS} = 10V	123A
100V	11.5mΩ @ V _{GS} = 6V	108A

Description

This new generation N-Channel Enhancement Mode MOSFET is designed to minimize $R_{DS(ON)}$, yet maintain superior switching performance. This device is ideal for use in notebook battery power management and load switch.

Applications

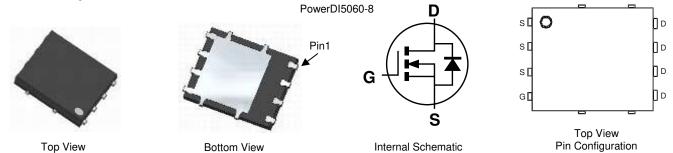
- Motor Control
- DC-DC Converters
- Power Management

Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures more reliable and robust end application
- Low R_{DS(ON)} Minimizes On-State Losses
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminal Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH10H010SPS-13	PowerDI5060-8	2,500/Tape & Reel

EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Notes:



D ! ! = Manufacturer's Marking TH10H010S = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 17 = 2017) WW = Week Code (01 to 53)

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	100	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current, V_{GS} = 10V (Note 5)	$T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$	۱ _D	11.8 8.3	А
Continuous Drain Current, V _{GS} = 10V (Note 6)	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	ID	123 87	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	250	А	
Maximum Continuous Body Diode Forward Current	Is	100	А	
Avalanche Current, L = 0.3mH	I _{AS}	33.7	А	
Avalanche Energy, L = 0.3mH	Eas	170	mJ	
Avalanche Current (Note 7), L = 3mH	I _{AS}	14.3	A	
Avalanche Energy (Note 7), L = 3mH		E _{AS}	307	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)		R _{0JA}	99	°C/W
Total Power Dissipation (Note 6)	T _C = +25°C	PD	166	W
Thermal Resistance, Junction to Case (Note 6)	R _{ejc}	0.9	°C/W	
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +175	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

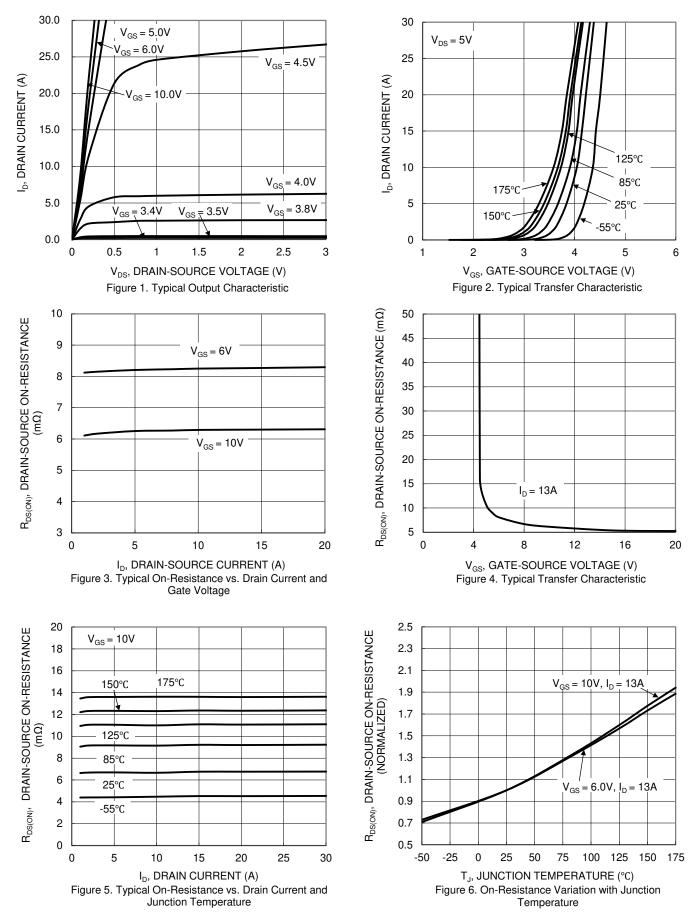
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	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)		100	r	1		
Drain-Source Breakdown Voltage	BV _{DSS}	100	—	—	V	$V_{GS} = 0V, I_D = 1mA$
Zero Gate Voltage Drain Current	I _{DSS}	_	—	1	μA	$V_{DS} = 80V, V_{GS} = 0V$
Gate-Source Leakage	IGSS	_	—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	2	—	4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance	D	—	6.6	8.8	mΩ	V _{GS} = 10V, I _D = 13A
Static Drain-Source On-Resistance	R _{DS(ON)}	_	8.5	11.5	11122	$V_{GS} = 6V, I_D = 13A$
Diode Forward Voltage	V _{SD}	_	0.8	1.3	V	V _{GS} = 0V, I _S = 13A
DYNAMIC CHARACTERISTICS (Note 8)						-
Input Capacitance	CISS	—	4,468	_		$V_{DS} = 50V, V_{GS} = 0V$ f = 1MHz
Output Capacitance	Coss	_	746		pF	
Reverse Transfer Capacitance	C _{RSS}	_	32	_		
Gate Resistance	R _G	_	0.91	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge	Q _G	_	56.4	_		
Gate-Source Charge	Q _{GS}	_	15.4	_	nC	$V_{DD} = 50V, I_D = 13A,$
Gate-Drain Charge	Q _{GD}	—	14	—		$V_{GS} = 10V$
Turn-On Delay Time	t _{D(ON)}	—	18.6	—		V _{DD} = 50V, V _{GS} = 10V,
Turn-On Rise Time	t _R	—	22.5	_	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	44.8		115	$I_D = 13A, R_g = 6\Omega$
Turn-Off Fall Time	t⊨		29.5			
Reverse Recovery Time	t _{RR}	—	54.5		ns	l = -120 di/dt = 1000/us
Reverse Recovery Charge	Q _{RR}		106.4	_	nC	I _F = 13A, di/dt = 100A/μs

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

Bevice interview of the transmission recommended participation, and
 Chermal resistance from junction to soldering point (on the exposed drain pad).
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

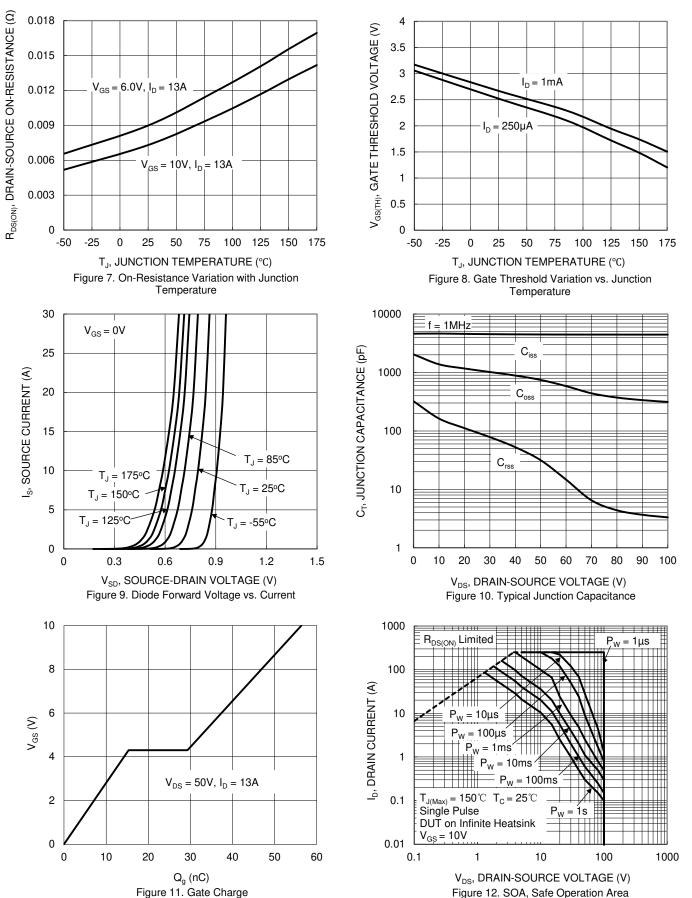


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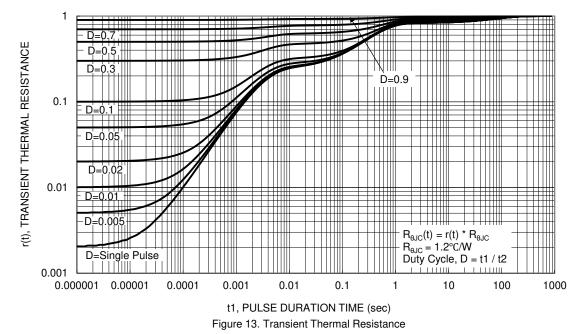


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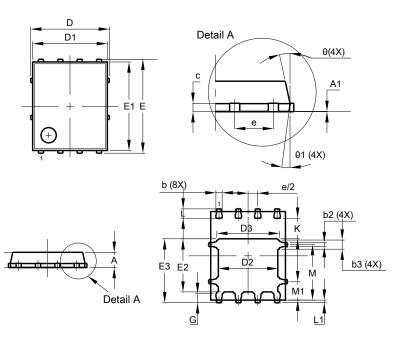






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



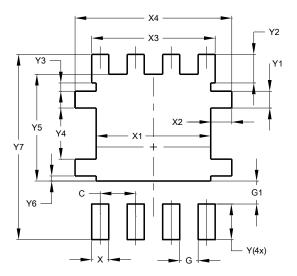
PowerDI5060-8

PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D	5.15 BSC				
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
E	6.15 BSC				
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
e	1.27 BSC				
G	0.51	0.71	0.61		
K	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
М	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
Al	All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
Х	0.610			
X1	4.100			
X2	0.755			
X3	4.420			
X4	5.610			
Y	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
¥7	6.610			



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